

LIST OF FIGURES

Chapter 2

- Figure 2.1** Schematic showing (A) a magnetic semiconductor, (B) a non-magnetic semiconductor material, and (C) a diluted magnetic semiconductor (adapted from ref. 7)..... 6
- Figure 2.2** Bulk structure of rutile and anatase. The tetragonal bulk unit cell of rutile has the dimensions, $a = b = 4.587 \text{ \AA}$, $c = 2.953 \text{ \AA}$, and the one of anatase $a = b = 3.782 \text{ \AA}$, $c = 9.502 \text{ \AA}$. In both structures, slightly distorted octahedra are the basic buildings units. The bond lengths and angles of the octahedrally coordinated Ti atoms are indicated and the stacking of the octahedra in both structures is shown on the right hand side (adapted from ref. 32)..... 9
- Figure 2.3** The $M-T$ data for a $\text{Ti}_{0.93}\text{Co}_{0.07}\text{O}_{2-\delta}$ film. The inset shows the hysteresis loops obtained under zero-field cooling (ZFC) and field cooling (FC) conditions (from ref. 40)..... 13
- Figure 2.4** Magnetization hysteresis loops for $\text{Ti}_{1-x}\text{Co}_x\text{O}_2$ thin films with Co contents of $x=0.03$ (a), $x=0.05$ (b), $x=0.07$ (c), $x=0.12$ (d). Plots (a), (b): films with no Co clusters; plots (c), (d): films with Co clusters. Scheme below: microstructural model representing the influence of Co content on the magnetic properties of $\text{Ti}_{1-x}\text{Co}_x\text{O}_2$ thin films. FM stands for ferromagnetic and SM for soft magnetic behaviour. Adapted from ref. 47..... 15
- Figure 2.5** The temperature dependence of the resistivity for: (a) a 600 nm thick undoped TiO_2 film, (b) a 200 nm thick 7% Co: TiO_2 film, and (c) a 1200 nm thick 7% Co: TiO_2 film (from ref. 43)..... 16
- Figure 2.6** Magnetoresistance as a function of magnetic field for undoped TiO_2 and $\text{Ti}_{1-x}\text{Co}_x\text{O}_{2-\delta}$ films (from ref. 40)..... 17
- Figure 2.7** Polaron percolation model as illustrated by Coey *et al.* (from ref. 23) 19

Chapter 3

- Figure 3.1** Schematic illustrating key elements of the pulsed laser ablation event. (a) Initial absorption of laser radiation (indicated by long arrows), melting and vaporization begin (shaded area indicates melted material, short arrows indicate motion of solid-liquid interface). (b) Melt front propagates into the solid, vaporization continues and laser-plume interactions start to become important. (c) Absorption of incident laser radiation by the plume, and plasma formation. (d) Melt front recedes leading to eventual re-solidification..... 33
- Figure 3.2** Schematic presentation of the pulsed laser deposition process..... 34
- Figure 3.3** Schematic diagram of atomic processes in the nucleation of three dimensional clusters of deposited film atoms on a substrate surface..... 43

Chapter 4

Figure 4.1 Schematic front view of the deposition set-up.....	49
Figure 4.2 Typical beam profile (variation in intensity across the beam) for an excimer laser. Axis scales depend on the type of exciplex.....	51
Figure 4.3 General view of the (vacuum) PLD chamber.....	53
Figure 4.4 Detailed cross-section view of the vacuum chamber.....	54
Figure 4.5 Substrate heating holder: a) Schematic side view; b) Detailed cross-section view.....	57
Figure 4.6 Calibration curve for Al ₂ O ₃ (0001) substrate temperature.....	57
Figure 4.7 General view of the target holder.....	58
Figure 4.8 A Bragg reflection from a particular family of lattice planes, separated by a distance d . Incident and reflected rays are shown for two neighbouring planes. The path difference is $2d \sin \theta$	63
Figure 4.9 Effect of fine crystallite size on diffraction lines. a) (hkl) diffraction peak from an infinite crystal with a perfect 3D order (hypothetical case); b) peak broadening due to small crystallite size.....	64
Figure 4.10 XRD pattern of the Co-doped TiO ₂ target used for the deposition of the films...	65
Figure 4.11 RBS spectrum from a thin film on a substrate.....	69
Figure 4.12 Scheme of the optical path and components of the Shimadzu UV-Visible Spectrophotometer. D2: deuterium lamp; WI: halogen lamp; W: window plate; M1 – M5: mirrors (M3 is a half-mirror); S1/S2: entrance/exit slits; G: grating; F: filter; Sam.: sample cell; Ref.: reference cell; L: lens; P.D.: photodiode.....	71
Figure 4.13 An absorbing thin film on a thick, finite, transparent substrate.....	73
Figure 4.14 Transmittance spectrum of a Co-doped TiO ₂ thin film deposited on Al ₂ O ₃ (0001) substrate.....	73
Figure 4.15 Variation of the refractive index of rutile ^{23,24} with the wavelength.....	75
Figure 4.16 Absorption coefficient α versus λ for different Co-doped TiO ₂ thin films deposited onto Al ₂ O ₃ (0001) substrate.....	77
Figure 4.17 $(\alpha h\nu)^{1/2}$ versus $h\nu$ for different Co-doped TiO ₂ thin films deposited onto Al ₂ O ₃ (0001) substrate, and linear fit to the high energy region allowing the determination of the optical energy band gap.....	77
Figure 4.18 a) Four-point probe arrangement for measuring sheet resistance of a thin film; b) geometry defining the sheet resistance of a film of thickness d , length l and width b	78

Chapter 5

- Figure 5.1** XRD patterns of Co-doped TiO₂ films grown on (0001) Al₂O₃ substrates in an Ar atmosphere, $P_T = 5.0 \times 10^{-1}$ mbar, at different laser energies, from 52 to 195 mJ at substrate temperature, $T_S = 250$ °C..... 83
- Figure 5.2** XRD patterns of Co-doped TiO₂ films grown on (0001) Al₂O₃ substrates in an Ar atmosphere, $P_T = 5.0 \times 10^{-1}$ mbar, at different laser energies, from 53 mJ to 157 mJ at substrate temperature, $T_S = 310$ °C..... 84
- Figure 5.3** Mean crystallite size of Co-doped TiO₂ films deposited on (0001) Al₂O₃ substrates as a function of laser output energy. The curve drawn through the data points is for guidance only..... 84
- Figure 5.4** Optical transmittance spectra of Co-doped TiO₂ films grown in Argon environment at $T_S = 250$ °C for laser output energies of 157 and 195 mJ (a) and 52 and 95 mJ (b). In (c), the films were grown at $T_S = 310$ °C for various laser output energies..... 86
- Figure 5.5** Photon energy dependence of SQRT($\alpha h\nu$) for Co-doped TiO₂ films, identified through their labels. Straight lines represent linear fits to the high energy region of the curves. Values for the band gap of the films are also shown in the figures. Left panel: $T_S = 250$ °C; right panel: $T_S = 310$ °C..... 87
- Figure 5.6** RBS spectra of Co-doped TiO₂ thin films deposited on (0001)Al₂O₃ substrate recorded for ⁴He⁺ incident energy of 2 MeV (top) and ¹H⁺ incident energy of 2 MeV (bottom), and the corresponding theoretical simulations..... 88
- Figure 5.7** Film thickness deposited per laser pulse vs. Argon pressure..... 91
- Figure 5.8** XRD θ - 2θ scanning patterns of Co-doped TiO₂ thin films grown on (0001) Al₂O₃ substrates, at total pressures ranging from 7.0×10^{-1} mbar to 7.0×10^{-2} mbar. $\Phi_{Ar} = 30$ sccm, $T_S = 310$ °C, laser frequency = 20 Hz, and $F = 6.4$ J/cm²..... 92
- Figure 5.9** XRD θ - 2θ scanning patterns of Co-doped TiO₂ thin films grown on (0001) Al₂O₃ substrates, at total pressures ranging from 2.5×10^{-1} mbar to 7.5×10^{-1} mbar. $\Phi_{Ar} = 30$ sccm, $T_S = 250$ °C, laser frequency = 20 Hz, and $F = 7.9$ J/cm²..... 92
- Figure 5.10** FWHM (θ - 2θ scan) of the Bragg reflection peak vs. total pressure..... 95
- Figure 5.11** Optical transmittance spectra (a) and average transmission, $T_{av.}$, vs. Pressure (b) for Co-doped TiO₂ films grown in Ar environment at various total pressures, $E_{laser} = 157$ mJ and $T_S = 310$ °C 96
- Figure 5.12** Photon energy dependence of the SQRT($\alpha h\nu$) for the Co-doped TiO₂ films deposited under the conditions described in Table 5.3. Straight lines represent linear fits to the high energy region of the curves. Values for the band gap of the films are also shown in the figure..... 96
- Figure 5.13** Optical transmittance spectra (a) and average transmission, $T_{av.}$, vs. pressure (b) for Co-doped TiO₂ films grown in Ar environment at various total pressures, $E_{laser} = 195$ mJ and $T_S = 250$ °C..... 98
- Figure 5.14** RBS spectra of samples F63 (left) and F52 (right) deposited on (0001)Al₂O₃

substrate and the corresponding theoretical simulations. The spectra were recorded with $^1\text{H}^+$ incident energy of 2 MeV.....	99
Figure 5.15 RBS spectra of sample F84 deposited on (0001) Al_2O_3 substrate recorded for $^4\text{He}^+$ incident energy of 2 MeV and the corresponding theoretical simulation.....	100
Figure 5.16 RBS spectra of samples F42 and F56 deposited on (0001) Al_2O_3 substrate. Left panel spectrum was recorded for $^4\text{He}^+$ incident energy of 2 MeV while on the right panel $^1\text{H}^+$ incident energy of 2 MeV was used. The RUMP simulations are also plotted.....	101
Figure 5.17 XRD patterns of Co-doped TiO_2 films grown on (0001) Al_2O_3 substrates in an Ar atmosphere, $P_{\text{T}} = 5.0 \times 10^{-1}$ mbar, at different substrate temperatures.....	102
Figure 5.18 Optical transmittance spectra a) and Tauc plot b) for the Co-doped TiO_2 films displayed in Fig. 5.17.....	103
Figure 5.19 XRD θ - 2θ scanning patterns of Co-doped TiO_2 thin films grown on (0001) Al_2O_3 substrates, at argon fluxes, Φ_{Ar} , ranging from 6 to 270 sccm. The substrate temperature, pulse repetition rate and laser fluence were kept constant at 310 °C, 20 Hz and 5.1 J/cm ² , respectively. Total pressure is 5.0×10^{-1} mbar.....	104
Figure 5.20 Argon flux favours the rutile phase growth relative to that of anatase phase. The dashed line is for visual guidance only.....	106
Figure 5.21 XRD θ - 2θ scanning patterns of Co-doped TiO_2 thin films grown on (0001) Al_2O_3 substrates, at argon fluxes, $\Phi_{\text{Ar}} = 6$ and 270 sccm. The substrate temperature, pulse repetition rate and laser fluence were kept constant at 310 °C, 20 Hz and 5.1 J/cm ² , respectively. Total pressure is 7.0×10^{-2} mbar. Right panel: magnification of the 2θ range: 38–44°.....	107
Figure 5.22 Optical transmittance spectra of Co-doped TiO_2 films grown in Ar environment at a) $P_{\text{T}} = 5.0 \times 10^{-1}$ mbar, b) $P_{\text{T}} = 7.0 \times 10^{-2}$ mbar.....	108
Figure 5.23 Photon energy dependence of the square root of $(\alpha h\nu)$ for the Co-doped TiO_2 films deposited under the conditions described in Figs. 5.22-a and 5.22-b. Straight lines represent linear fits to the high energy region of the curves. Values for the band gaps of the films are also shown in the figure.....	109
Figure 5.24 Band gap energy, E_{g}^{i} , versus Ar flux for Co-doped TiO_2 thin films deposited at $P_{\text{T}} = 5.0 \times 10^{-1}$ mbar and 7.0×10^{-2} mbar, respectively.....	109
Figure 5.25 (a) XRD patterns of Co-doped TiO_2 thin films deposited on (0001) Al_2O_3 at a total pressure of 1.0×10^{-1} mbar with an argon flow rate of 30 sccm and $T_{\text{S}} = 200$ °C. (b) The asymmetric peak at about $2\theta = 38.81^\circ$ was resolved into two peaks: R(200) at $2\theta = 38.89^\circ$ and A(112) at $2\theta = 38.65^\circ$. Labelled lines were taken from JCPDS file cards no. 21-1272 for anatase and 21-1276 for rutile.....	111
Figure 5.26 a) Variation of $[A_{112}] / [R_{200}]$ intensity ratio with hydrogen flux for samples grown at $T_{\text{S}} = 200$ °C. b) Volume of the unit cell vs. hydrogen flow rate for the same samples as in a). Dashed lines are for visual guidance only.....	112
Figure 5.27 a) XRD patterns of Co-doped TiO_2 thin films deposited on (0001) Al_2O_3 at a total pressure of 1.0×10^{-1} mbar with an argon flow rate of 30 sccm and $T_{\text{S}} = 310$ °C. b) PsVoigt fit of R(200) at $2\theta = 39.29^\circ$. The H_2 flow rates are indicated in the figure. Labelled lines were	

taken from JCPDS file card no. 21-1276 for rutile.....	113
Figure 5.28 Optical transmittance spectra of Co:TiO ₂ films grown in Ar/H ₂ environment at 1.0×10 ⁻¹ mbar, for various H ₂ flow rates; substrate temperature: T _S = 310 °C (left) and T _S = 200 °C (right).....	114
Figure 5.29 Photon energy dependence of SQRT (αhv) for the Co-doped TiO ₂ films deposited under the conditions described in Fig. 5.28. Straight lines represent linear fits to the high energy region of the curves. Values for the band gap of the films are also shown in the figure.....	115
Figure 5.30 Layered structure model used to fit the SE data.....	116
Figure 5.31 Refractive index (left panels) and extinction coefficient (right panels) of the bulk layer of the Co-doped TiO ₂ films, as a function of H ₂ flow rate for two substrate temperatures, T _S	118
Figure 5.32 Refractive index (left panels) and extinction coefficient (right panels) of the surface layer of the Co-doped TiO ₂ films, as a function of H ₂ flow rate for two substrate temperatures, T _S	119
Figure 5.33 a) RBS and b) ERDA spectra of sample F94 recorded for ⁴ He ⁺ incident energy of 2 MeV and the corresponding theoretical simulations.....	121
Figure 5.34 AFM image (2.0 μm×2.0 μm) of the surface morphology of a Co-doped TiO ₂ film deposited at T _S = 310 °C and Φ _{H2} = 1 sccm.....	123
Figure 5.35 Band gap energy as a function of hydrogen flow rate. Inset: resistivity vs. hydrogen flux.....	124
Figure 5.36 a) Magnetization M(μ _B /formula unit) versus applied magnetic field for sample F94 (T _S = 310 °C, P _T = 1.0×10 ⁻¹ mbar, Φ _{Ar} = 30 sccm and Φ _{H2} = 0.1 sccm), recorded at various temperatures; b) Saturation magnetization, M _S , as a function of temperature. The solid line is provided as a visual guide.....	125
Figure 5.37 MCD of a 2.1 μm thick film on an (0001) Al ₂ O ₃ substrate, at 10 K in a field of 0.45 T.....	126

